

# **V1.11 Datasheet**

#### **N-Channel 40V MOSFET**

#### **FEATURES**

- Advance Trench Process Technology
- ●High Density Cell Design for Ultra Low On-resistance

PRODUCTY SUMMARY						
$V_{DS}(V)$ $I_{D}(A)$ $R_{DS(on)}m(\Omega)$ Max						
40	600	1.1	@V <sub>GS</sub> =10V			
40	000	1.5	@V <sub>GS</sub> =4.5V			

# **Application**

- ●DC/DC converters
- Battery Protection
- ●Consumer Electronics

#### Mechanical

●Case:TOLL Package

# **TOLL**



## **Packing Information**

Package	Packing
TOLL	2000EA/13" Reel

Maximum Ratings (T <sub>A</sub> =25°C unless otherwise specified)								
Parameter Symbol Limit								
Drain-Source Voltage	V <sub>DS</sub>	40	V					
Gate-Source Voltage	V <sub>GS</sub>	±20	V					
Drain Current, V <sub>GS</sub> @10V (Silicon Limited) 1)3)	I <sub>D</sub>	600	А					
Drain Current, V <sub>GS</sub> @10V (Wire Bond Limited) 1)3)	I <sub>D</sub>	400	А					
Peak Drain Current, Pulsed 1)2)3)	I <sub>DM</sub>	640	А					
Maximum Power Dissipation 1)	P <sub>tot</sub>	500	W					
Operating Junction and Storage Temperature Range	$T_J, T_STG$	-55 to 175	°C					

Typical Thermal Resistance							
Parameter Symbol Limit Unit							
Junction-to-Ambient Thermal Resistance 1)	$R_{\theta JA}$	42	°C/W				
Junction-to-Ambient Thermal Resistance 1)	$R_{\theta JC}$	0.25	°C/W				

### Note:

- 1. Surface Mounted on a 1 in2 pad area, t≦10sec
- 2. Pulse width≦300us, Duty cycle≦2%.
- Limited by bonding wire
   Essentially independent of operating temperature typical characteristics.
- 5. Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial  $T_J$  =25°C.
- 6. The maximum current rating is package limited.
- Guaranteed by design, not subject to production testing.



Electrical Characteristics (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)						
Characteristics	Symbol	Test Condition		Limits		
	Syllibol	rest Condition	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$B_{VDSS}$	$V_{GS}$ =0V, $I_D$ =250uA	40	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250uA$	1.00	1.50	2.50	V
Drain-Source On-State Resistance	D	V <sub>GS</sub> =10.0V, I <sub>D</sub> =95.0A	-	-	1.1	mΩ
	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =20.0A	-	-	1.5	mΩ
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V	-	-	1.0	uA
GateSource Leakage Current	I <sub>GSS</sub>	$V_{GS}$ =±20V, $V_{DS}$ =0V	-	-	±100	nA

Dynamic <sup>2)</sup>						
Total Gate Charge	Qg	V <sub>DS</sub> =20V, V <sub>GS</sub> =10V, I <sub>D</sub> =1.0A	-	352	-	nC
Total Gate Charge	Qg		-	171	-	nC
Gate-Source Charge	$Q_{gs}$	$V_{DS}$ =20V, $V_{GS}$ =4.5V, $I_{D}$ =1.0A	-	38	-	nC
Gate-Drain Charge	$Q_{gd}$		-	66	-	nC
Gate resistance	R <sub>G</sub>		-	0.82	-	Ω
Input Capacitance	C <sub>iss</sub>	\/ _20\/ \/ _0\/ <del>f</del> _200KH <del>-</del>	-	21865	-	pF
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ =20V, $V_{GS}$ =0V, f=200KHz	-	1190	-	pF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	1155	-	pF

Switching						
Turn-On Delay Time	t <sub>d(on)</sub>		-	53	-	ns
Turn-On Rise Time	t <sub>r</sub>	$V_{DS}$ =20V, $R_{L}$ =10.0 $\Omega$ ,	-	36	-	ns
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GEN}$ =10V, $R_{G}$ =3.0 $\Omega$	-	357	-	ns
Turn-Off Fall Time	t <sub>f</sub>		-	100	-	ns

Drain-Source Diode						
Body-Diode Continuous Current	Is	-	-	-	160	A
Diode Forward Voltage 1)	$V_{SD}$	I <sub>SD</sub> =50A, V <sub>GS</sub> =0V	-	-	1.3	V

Note:

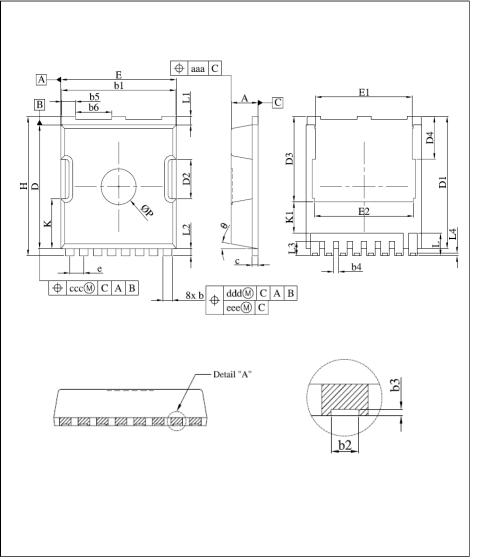
1. Pulse width<300us, Duty cycle<2%.

2. Guaranteed by design, not subject to production testing.



### Package Outline Dimensions (inches and millimeters)

TOLL						
	Dimensions					
SYMBOL	Millim	neters	Inc	hes		
	Min	Max	Min	Max		
Α	2.20	2.40	0.087	0.094		
b	0.70	0.90	0.028	0.035		
b1	9.70	9.90	0.382	0.390		
b2	0.36	0.55	0.014	0.022		
b3	0.05	0.35	0.002	0.014		
b4	0.30	0.50	0.012	0.020		
b5	1.10	1.30	0.043	0.051		
b6	3.00	3.20	0.118	0.126		
С	0.40	0.60	0.016	0.024		
D	10.28	10.55	0.405	0.415		
D1	10.98	11.18	0.432	0.440		
D2	3.20	3.40	0.126	0.134		
D3	7.00	7.30	0.276	0.287		
D4	3.44	3.74	0.135	0.147		
е	1.10	1.30	0.043	0.051		
E	9.80	10.00	0.386	0.394		
E1	8.20	8.40	0.323	0.331		
E2	8.35	8.65	0.329	0.341		
Н	11.50	11.85	0.453	0.467		
K	4.08	4.28	0.161	0.169		
K1	2.45	-	0.096	-		
L	1.60	2.10	0.063	0.083		
L1	0.50	0.90	0.020	0.035		
L2	0.50	0.70	0.020	0.028		
L3	1.00	1.30	0.039	0.051		
L4	0.13	0.33	0.005	0.013		
Р	2.85	3.15	0.112	0.124		
θ		10°	REF.			
aaa	0.2		0.008			
CCC	0.2	20	0.0	800		
ddd	0.2	25	0.0	10		
666	0.2	20	0.0	08		



### **Marking Information**



First line = Company name

MSN01140A = Product number

XXXXXXX = Tracking number

Fourth line = Gate pin point

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